

FORM PTO-1449/A and B (Modified)		MAR 1 2 2002		APPLICATION NO.: 10/020,047	ATTY. DOCKET NO.: M0635/7073
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				FILING DATE: December 7, 2001	
				APPLICANT: Rothschild et al.	
				GROUP ART UNIT: Not Yet Assigned	EXAMINER: Not Yet Assigned
Sheet	1	of	1		

U.S. PATENT DOCUMENTS

Examiner's Initials#	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication or of issue of Cited Document MM-DD-YYY
		Number	Kind Code		
<i>[Signature]</i>		5,667,919		Tu et al.	09-16-1997
<i>[Signature]</i>		5,928,813		Krivokapic et al.	07-27-1999
<i>[Signature]</i>		5,939,227		Smith	08-17-1999
<i>[Signature]</i>		5,981,109		Tu et al.	11-09-1999

FOREIGN PATENT DOCUMENTS

Examiner's Initials#	Cite No.	Foreign Patent Document			Name of Patentee or Applicant of Cited Document (not necessary)	Date of Publication of Cited Document MM-DD-YYYY	Translation (Y/N)
		Office/ Country	Number	Kind Code			
<i>[Signature]</i>		WO	00/42473		E.I. Du Pont de Nemours and Company	20-07-2000	--

OTHER ART — NON PATENT LITERATURE DOCUMENTS

Examiner's Initials#	Cite No	Include name of the author (in CAPITAL LETTERS) title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, relevant page(s), volume-issue number(s), publisher, city and/or country where published.	Translation (Y/N)
<i>[Signature]</i>		Saito et al., "Attenuated phase shift mask blanks with oxide or oxi-nitride of Cr or MoSi absorptive shifter," <u>Photomask and X-Ray Mask Technology</u> , SPIE Vol. 2254, April 22, 1994, pgs. 60-63.	
<i>[Signature]</i>		Jonckheere et al., "Molybdenum silicide based attenuated phase-shift masks," <u>J. Vac. Sci. Technol.</u> , B 12(6), Nov/Dec. 1994, pages 3765-3772.	
<i>[Signature]</i>		Chen et al., "Silicon-Oxynitride Films Prepared for 157 nm Attenuated Phase Shifting Masks," <u>Optical Microlithography XII</u> , SPIE Vol. 3679, March 17-19, 1999, pgs. 1085-1092.	
<i>[Signature]</i>		Onodera et al., "ZrSiO ₄ a new and robust material for attenuated phase-shift masks in ArF lithography," <u>BACUS Symposium on Photomask Technology</u> , SPIE Vol. 3873, September 1999, pgs. 337-343.	

EXAMINER <i>A. Rosasco</i>	DATE CONSIDERED <i>7/16/03</i>
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#EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

*a copy of this reference is not provided as it was previously cited by or submitted to the office in a prior application, Serial No. _____, filed _____, and relied upon for an earlier filing date under 35 U.S.C. 120 (continuation, continuation-in-part, and divisional applications).